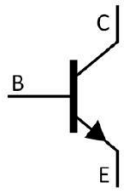
WR0459 Ṃ Ṃ Ꝉ QSQ Æ Ṁ ч s ǁ ᒣ Silicon NPN transistor in a TO-126 Plastic Package.

лъ EG56 ; Й ´
Complementary pair with BD238.

ᵮ ᴀ ı ' Ɔ ب ȝ Ã Ң Ɔ ب
Medium power linear and switching applications.



PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

ð м ᒣ ب ˝ See Marking Instructions.

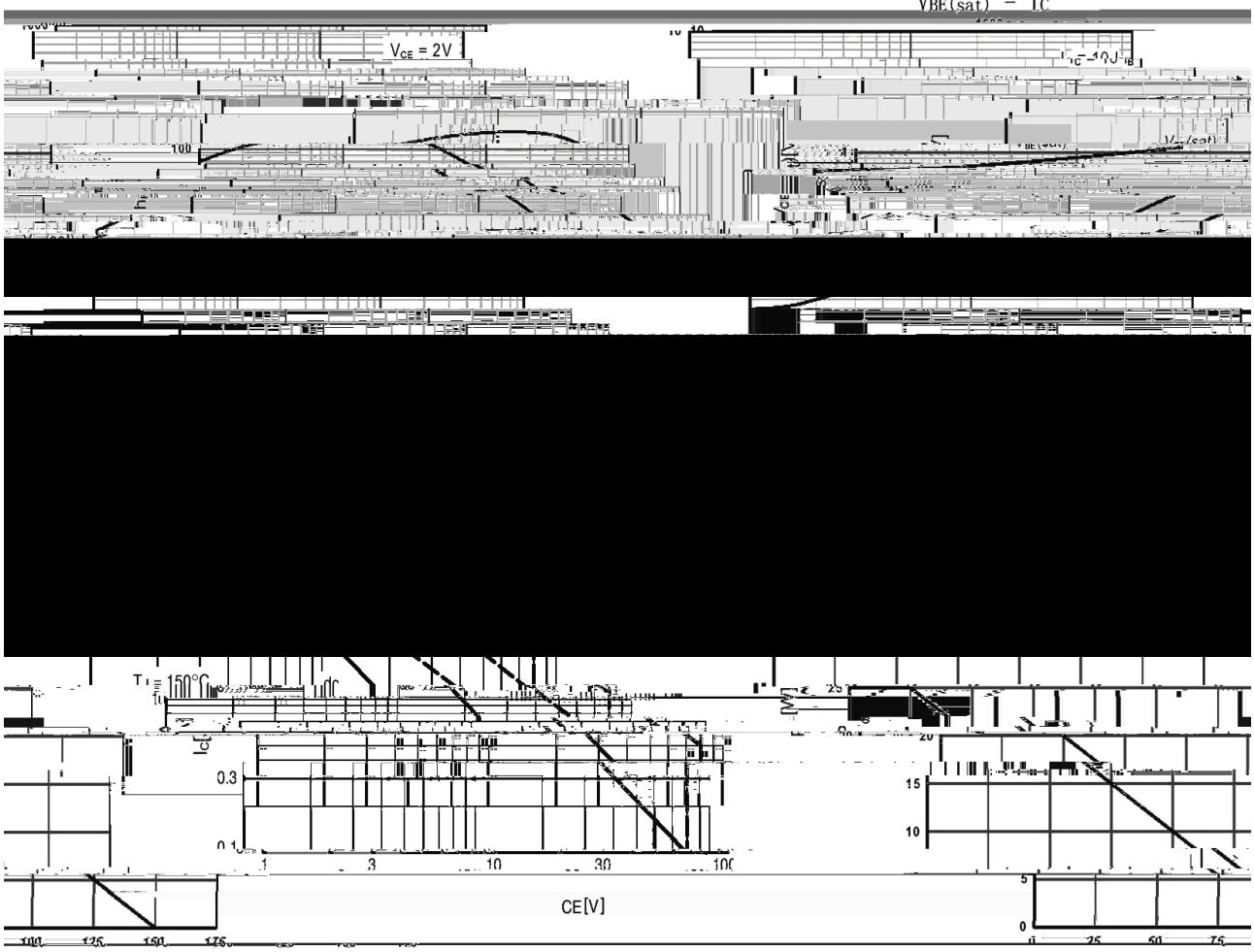
v ˝Ǫ Parameter	ϒ ᴺ Symbol	˝Ǫ Ö Rating	ᴅ Ꮋ Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Peak Collector Current	I_{CM}	6.0	A
Collector Power Dissipation	P_C(Tc=25)	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ˝Ǫ Parameter	ϒ ᴺ Symbol	⅄ ː ǂ ţ Test Conditions	ѡ ṇ Ö Ɛ ʒ Ö Min Á º ›

hFE – Ic

VCE(sat) – Ic

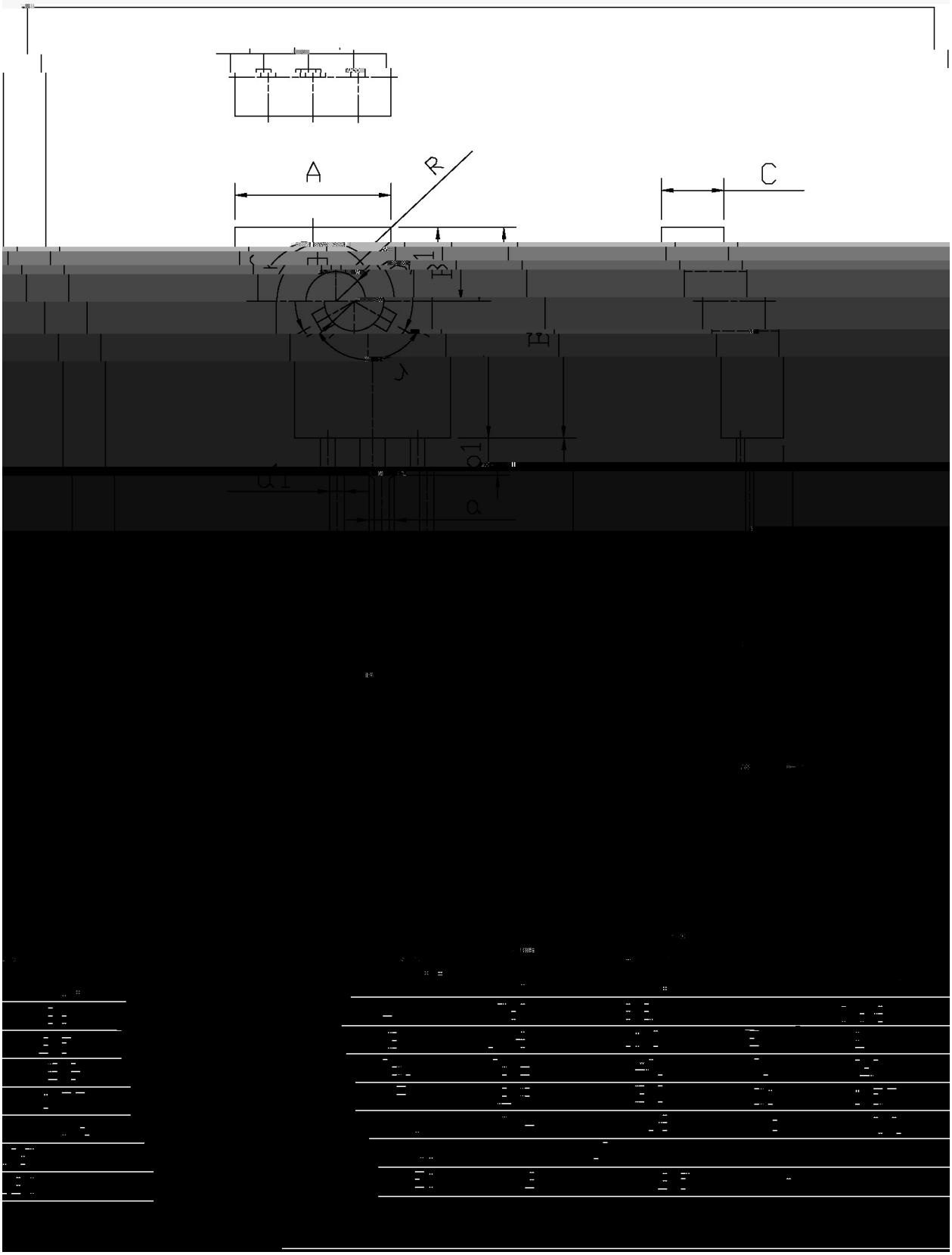
VBE(sat) – Ic

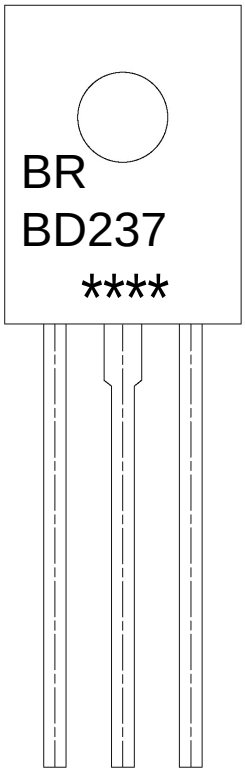


TC[°C]

TO-126

单位：mm





ᵕ̈ χ

EU χ ꟻ ʒ ᴎ Ꮆ

EG56 : χ ꟻ ꞙ β ȝ ᴺ

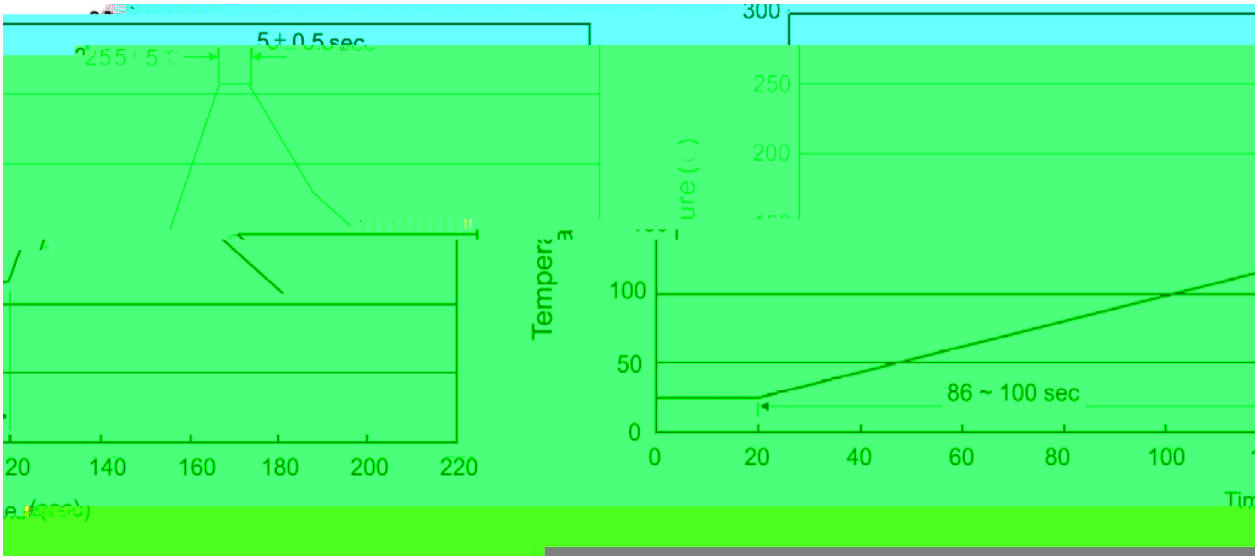
---- χ ꟻ ꞁ ꞙ ӈ̈ ᴺ Ꮆ ꞁ ҿ ꞁ ꞙ ӈ̈ ᴺ Ψ ᖘ

Note:

BR: Company Code

BD237: Product Type.

****: Lot No. Code, code change with Lot No.


5± 0.5sec
300
250
200
100
50
0
0
20
40
60
80
100
86 ~ 100 sec
20
140
160
180
200
220

Note: